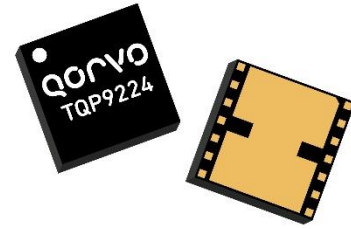


General Description

The TQP9224 is a high-linearity three-stage power amplifier in a low-cost surface-mount package with on-chip bias control and temperature control circuits, suitable for small cell or enterprise Femto cell base station applications.

The TQP9224 provides 36.7 dB high gain and -50 dBc ACLR at +24 dBm linear power using a 20 MHz LTE signal over the 2.3–2.4 GHz frequency range covering 3GPP Bands 30, 40.

The TQP9224 integrates three high performance amplifier stages to allow for a compact system design and requires very few external components for operation. The amplifier is bias adjustable allowing the amplifier's power consumption to be optimized for specific performance requirements. The TQP9224 is available in a lead-free/RoHS-compliant 7 x 7 mm surface mount package.

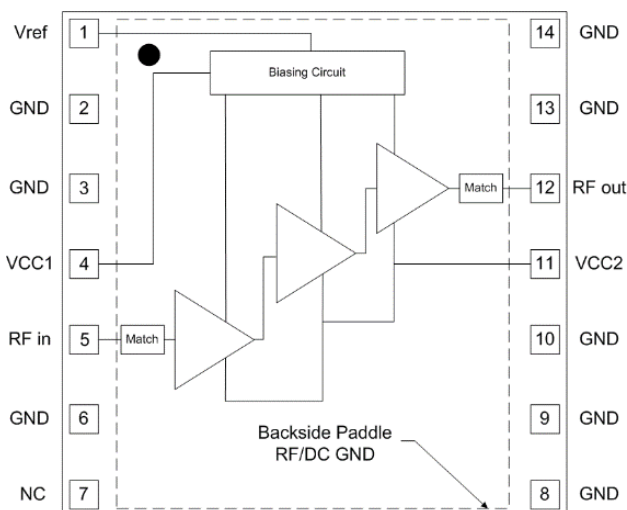


14 Pin 7 x 7 mm Leadless SMT Package

Product Features

- 2.3 – 2.4 GHz Frequency Range
- Fully integrated, 3-Stage Power Amplifier
- Internally Matched 50 Ω Input/Output
- -50 dBc ACLR at $P_{avg} = +24$ dBm
- 36.7 dB Gain
- 14% PAE at +24 dBm
- 204 mA Quiescent Current
- On-chip Control Bias and Temp. Comp Circuit
- RoHS compliant
- Covers Band 30, 40

Functional Block Diagram



Top View

Applications

- Small Cell / Picocell
- Enterprise Femtocell
- Customer Premises Equipment (CPE)
- Data Cards and Terminals
- Distributed Antenna Systems (DAS)
- Booster Amps, Repeaters

Ordering Information

| Part No. | Description |
|---------------|---------------------------------------|
| TQP9224TR13 | 2,500 pieces on a 13" reel (standard) |
| TQP9224PCB401 | 2.3–2.4 GHz Evaluation Board |

Absolute Maximum Ratings

| Parameter | Rating |
|-----------------------------------|----------------|
| Storage Temperature | -55 to +150 °C |
| RF Input Power, CW, 50Ω, T=+25 °C | +9 dBm |
| Supply Voltage (V _{CC}) | 6 V |
| V _{REF} | +3.5 V |

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability.

Recommended Operating Conditions

| Parameter | Min | Typ | Max | Units |
|---|-------|-------|-------|-------|
| V _{CC1} , V _{CC2} | +3.6 | +4.5 | +5.25 | V |
| V _{ref} | +2.75 | +2.85 | +2.95 | V |
| T _{CASE} | -40 | | +85 | °C |
| T _j at T _{CASE} max | | | +156 | °C |

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

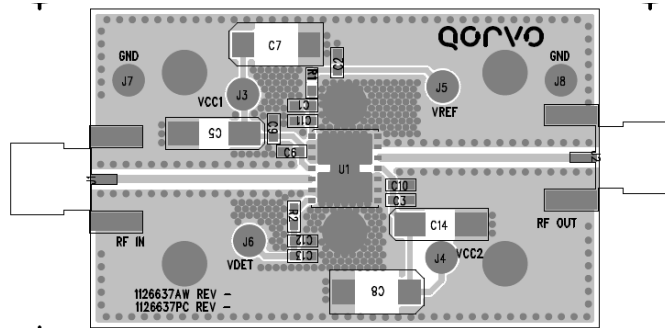
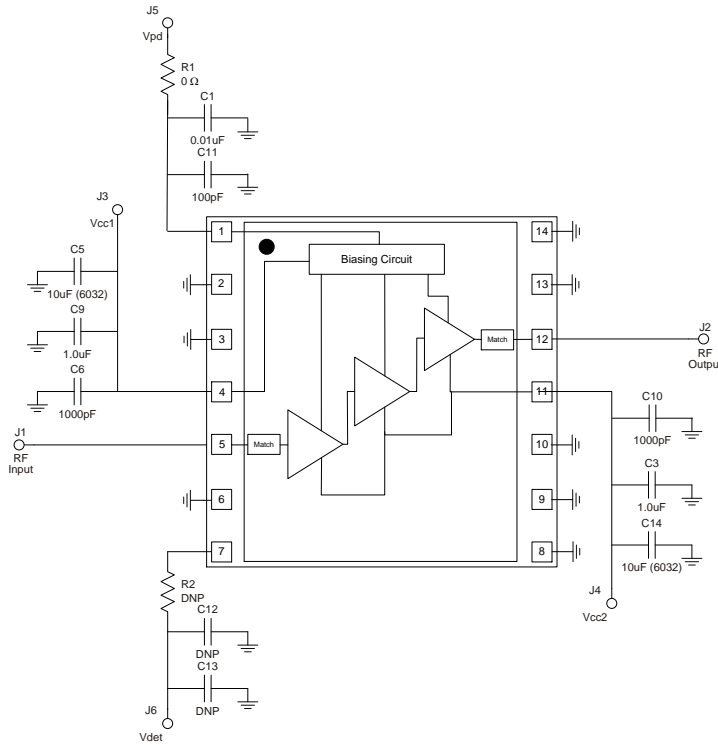
Electrical Specifications

| Parameter | Conditions ⁽¹⁾ | Min | Typ | Max | Units |
|--------------------------------------|--|------|-------|------|-------|
| Frequency Range | | 2300 | | 2400 | MHz |
| Test Frequency | | | 2350 | | MHz |
| Gain | | 34 | 36.7 | 40 | dB |
| Input Return Loss | | | 16 | | dB |
| Output Return Loss | | | 8 | | dB |
| Output P1dB | | | +33.6 | | dBm |
| ACLR | P _{OUT} = +24 dBm, 20 MHz LTE E-TM1.1, 9.5 dB PAR | | -50 | -45 | dBc |
| Power Added Efficiency | P _{OUT} = +24 dBm, 20 MHz LTE E-TM1.1, 9.5 dB PAR | 13 | 14 | | % |
| Spurious Output Level | P _{OUT} = +24 dBm, 10:1 VSWR | | <60 | | dBc |
| VSWR survivability | No permanent degradation or failure | 10:1 | | | - |
| Quiescent Current, I _{CCQ} | V _{CC1} + V _{CC2} | 160 | 204 | 250 | mA |
| Reference Current, I _{ref} | Temp = -40°C to +85°C, V _{REF} = +2.85V | | 8.7 | | mA |
| Leakage Current | V _{CC} = +4.5 V, V _{REF} = 0 V | | 1.5 | 8 | μA |
| Operational Current, I _{CC} | P _{OUT} = +24 dBm | | 390 | 430 | mA |
| Switching Speed | 0% V _{ref} to 90% RF Rise time | | 1.7 | 2.5 | μs |
| | 100% V _{ref} to 10% RF Fall time | | 0.87 | 1 | μs |
| Harmonics | 2F ₀ at +24dBm, CW signal | | -40 | -35 | dBc |
| | 3F ₀ at +24dBm, CW signal | | -54 | -49 | dBc |
| | 4F ₀ at +24dBm, CW signal | | -61 | -56 | dBc |
| Thermal Resistance, θ _{jc} | Module (junction to case) | | | 35.4 | °C/W |

Notes:

1. Test conditions unless otherwise noted: V_{CC1} = V_{CC2} = +4.5 V, V_{REF} = +2.85V, Temp = +25 °C, 50 Ω system.

Evaluation Board (TQP9224-PCB)

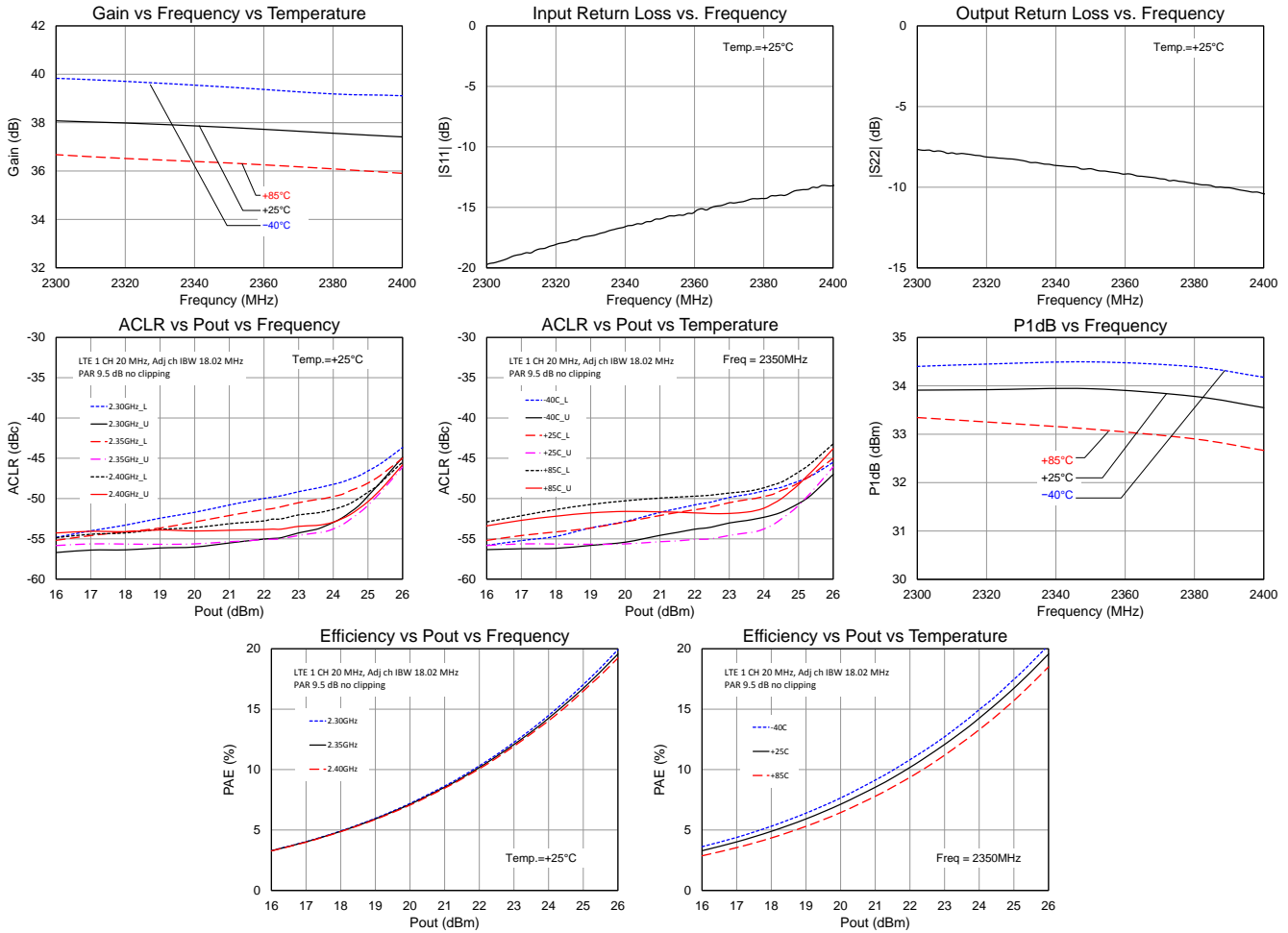


Bill of Material – TQP9224-PCB

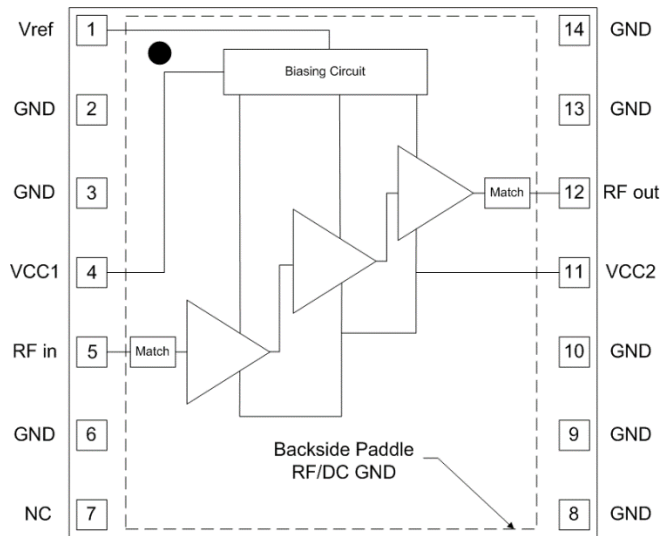
| Reference Des. | Value | Description | Manuf. | Part Number |
|----------------|------------|---------------------------------------|---------|-------------|
| n/a | n/a | Printed Circuit Board | | |
| U1 | n/a | High Linearity 0.25 W Power Amplifier | Qorvo | TQP9224 |
| R1 | 0 Ω | Resistor, Chip, 0603, 5% | various | |
| C1 | 0.01 uF | Capacitor, Chip, 0603, 5% | various | |
| C11 | 100 pF | Capacitor, Chip, 0603, 5% | various | |
| C3, C9 | 0.1 uF | Capacitor, Chip, 0603, 5% | various | |
| C5, C14 | 10 uF | Capacitor, Chip, 6032, 10%, Tantalum | various | |
| C6, C10 | 1000 pF | Capacitor, Chip, 0603, NPO/COG, 5% | various | |

Performance Plots

Test conditions unless otherwise noted: $V_{CC1} = V_{CC2} = +4.5V$, $V_{REF} = +2.85V$, $I_{CQ} = 204mA$, $I_{REF} = 8.7mA$, $Temp. = +25^\circ C$



Pin Configuration and Description

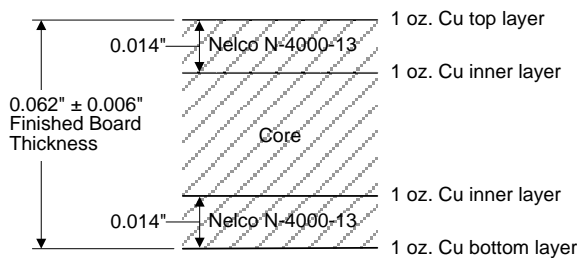


Top View

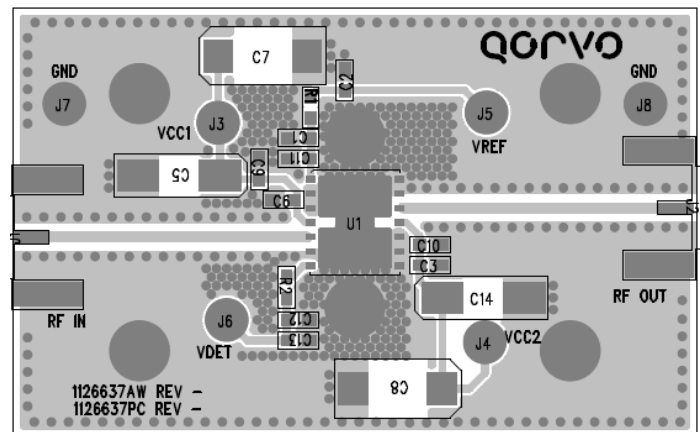
| Pad No. | Label | Description |
|---------------------------|------------------|---|
| 1 | V _{REF} | Sets the bias current for the amplifiers. It can also be used to power down the device. |
| 2, 3, 6, 8, 9, 10, 13, 14 | GND | RF and DC ground. |
| 4 | V _{CC1} | Voltage supply for the active bias circuitry. |
| 5 | RFin | RF input pin. The DC is internally blocked at this pin. |
| 7 | NC | No internal connection. |
| 11 | V _{CC2} | DC voltage supply connection for AMP1, 2, 3. |
| 12 | RFout | RF output pin. The DC is internally blocked at this pin. |
| Backside Paddle | RF/DC GND | RF/DC ground. See PCB Mounting Pattern for suggested footprint. |

Evaluation Board PCB Information

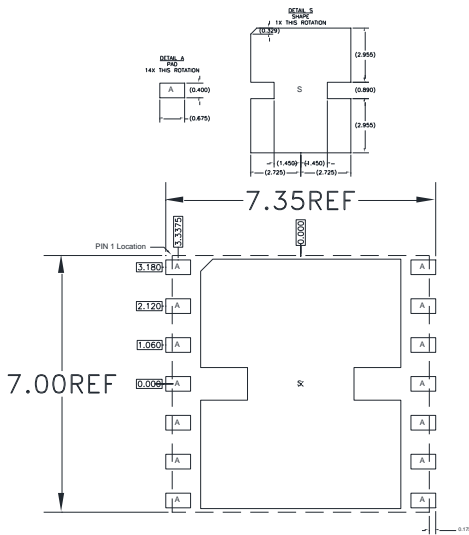
Qorvo PCB 1126637 Material and Stack-up



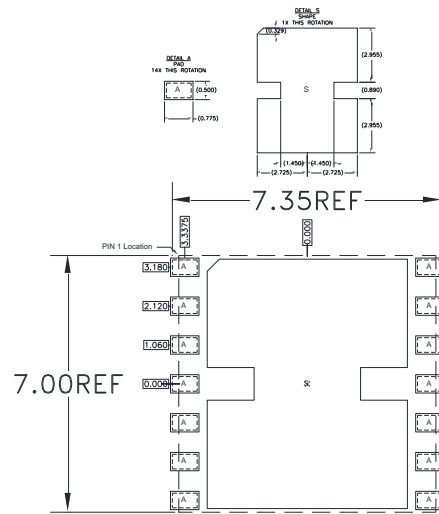
50 ohm line dimensions: width = .028"
spacing = .028".



PCB Mounting Pattern



RECOMMENDED
LAND PATTERN



RECOMMENDED
LAND PATTERN MASK

Notes:

1. All dimensions are in millimeters. Angles are in degrees.
2. Use 1 oz. copper minimum for top and bottom layer metal.
3. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. We recommend a 0.35mm (#80/.0135") diameter bit for drilling via holes and a final plated thru diameter of 0.25 mm (0.10").
4. Ensure good package backside paddle solder attach for reliable operation and best electrical performance.